

100V PNP LOW VCESAT TRANSISTOR IN PowerDI3333-8

Features

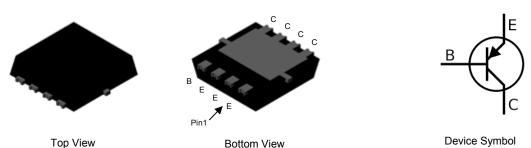
- BV_{CEO} > -100V
- Small Form Factor Thermally Efficient Package. Enables Higher Density End Products
- I_C = -5A Continuous Collector Current
- I_{CM} = -10A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < -90mV @ -1A •
- R_{SAT} = 56m Ω for a Low Equivalent On-Resistance
- hFE Specified up to -10A for a High Gain Hold-Up
- Complementary NPN Type: DXTN03100BFG
- Rated to +175°C Ideal For High Temperature Environment
- Wettable Flank For Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Plated Leads Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.03 grams (Approximate)

Applications

- Motor Driving
- Line Switching
- **High Side Switches**



PowerDI3333-8 (SWP) (Type UX)

Bottom View

Device Symbol

Ordering Information (Note 4)

Part Number Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DXTP03100BFG-7 2J9	7	12	2000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

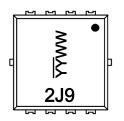
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/products/packages.html.

Marking Information

Notes:

PowerDI3333-8 (SWP) (Type UX)



2J9= Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 19 = 2019) WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-140	V
Collector-Emitter Voltage	V _{CEO}	-100	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ιc	-5	А
Peak Pulse Current	I _{CM}	-10	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Note 5)		1.07	W	
Power Dissipation	(Note 6)	PD	2.3	W	
	(Note 7)		3.4	W	
	(Note 5)		140	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	R _{OJA}	65	°C/W	
	(Note 7)		44	°C/W	
Thermal Resistance, Junction to Leads (Note 8)		R _{ƏJL}	6	°C/W	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +175	°C	

ESD Ratings (Note 9)

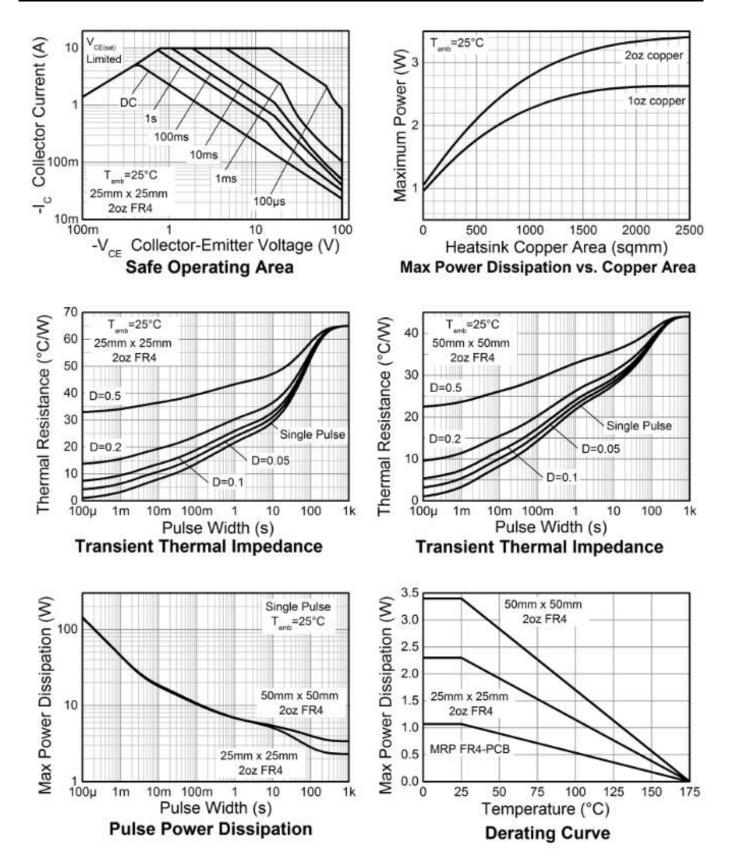
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

 For a device mounted with the collector tab on MRP FR4-PCB; device is measured under still air conditions whilst operating in a steady-state.
Same as Note 5, except the device is mounted on 25mm × 25mm 2oz copper.
Same as Note 5, except the device is mounted on 50mm × 50mm 2oz copper. Notes:

Thermal resistance from junction to solder-point (at the collector tab).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





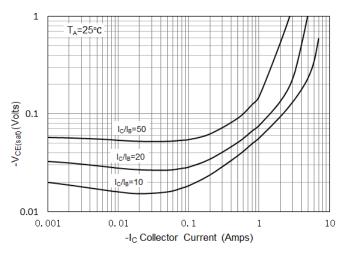
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-140	-169	_	V	I _C = -100μA
Collector-Emitter Breakdown Voltage	BVCER	-140	-167		V	$I_{\rm C}$ = -1µA, RB ≤ 1kΩ
Collector-Emitter Breakdown Voltage (Note 10)	BVCEO	-100	-125	_	V	$I_{\rm C}$ = -1mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.4	_	V	I _E = -100μA
Collector-Base Cut-Off Current	I _{CBO}		-2	-50	nA	V _{CB} = -100V
Collector-Base Cut-Off Current		-	-0.1	-10	μA	V _{CB} = -100V, T _A = +125°C
Collector-Emitter Cut-Off Current	ICER	_	-2	-50	nA	V _{CB} = -100V
Collector-Emitter Cut-On Current	R ≤ 1kΩ		-0.3	-10	μA	V _{CB} = -100V, T _A = +125°C
Emitter Cut-Off Current	I _{EBO}		1	-20	nA	V _{EB} = -6V
	h _{FE}	100	172	_		I _C = -10mA, V _{CE} = -2V
		100	151	300	_	I _C = -1A, V _{CE} = -2V
Static Forward Current Transfer Ratio (Note 10)		25	43	_	_	I _C = -3A, V _{CE} = -2V
		15	27	_	_	I _C = -4A, V _{CE} = -2V
		5	7.3	_	_	I _C = -10A, V _{CE} = -2V
	V _{CE(sat)}	_	-18	-30	mV	I _C = -100mA, I _B = -10mA
Collector Emitter Saturation Voltage (Note 10)		_	-56	-90	mV	I _C = -1A, I _B = -100mA
Collector-Emitter Saturation Voltage (Note 10)		_	-94	-150	mV	I _C = -2A, I _B = -200mA
		_	-177	-340	mV	I _C = -4A, I _B = -400mA
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	_	-967	-1100	mV	I _C = -4A, I _B = -400mV
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(on)}	-	-869	-950	mV	$I_{\rm C}$ = -4A, $V_{\rm CE}$ = -2V
Output Capacitance	Cobo	_	42	_	pF	V _{CB} = -10V. f = 1MHz
Transition Frequency	f _T	_	125	_	MHz	V _{CE} = -10V, I _C = -100mA f = 50MHz
	t _{delay}	_	10.1	_	ns	
Switching Characteristics	t _{rise}		181	_	ns	V _{CC} = -10V, I _C = -1A
Switching Characteristics	t _{storage}		1340	—	ns	I _{B1} = I _{B2} = -100mA
	t _{fall}	—	127	_	ns	

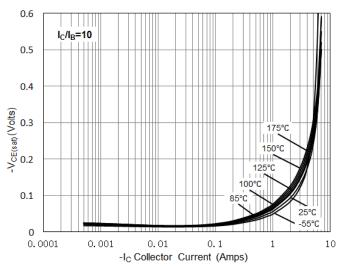
Note: 10. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



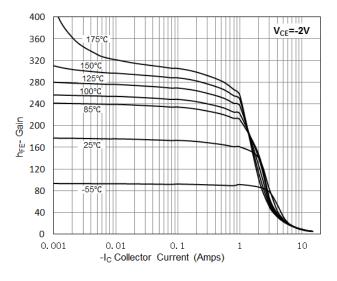
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



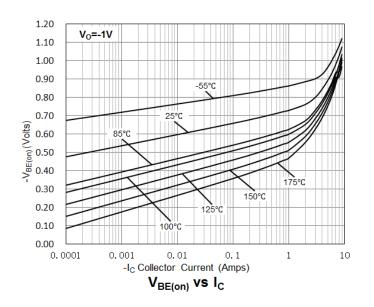
V_{CE(sat)} vs I_C

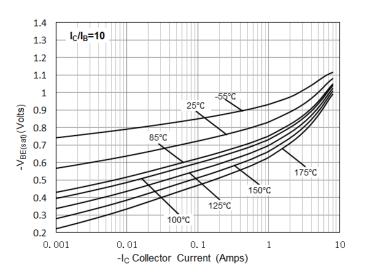


V_{CE(sat)} vs I_C









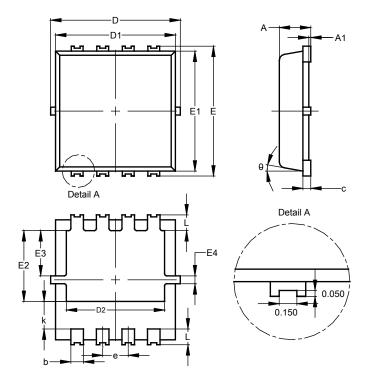
V_{BE(sat)} vs I_C



Package Outline Dimensions

Please see https://www.diodes.com/package-outlines.html for the latest version.

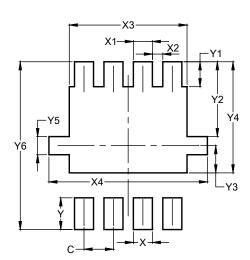
PowerDI3333-8 (SWP) (Type UX)



PowerDI3333-8 (SWP)					
(Type UX)					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
С	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E3	0.95	1.35	1.15		
E4	0.10	0.30	0.20		
е		_	0.65		
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All I	All Dimensions in mm				

Suggested Pad Layout

Please see https://www.diodes.com/package-outlines.html for the latest version.



PowerDI3333-8 (SWP) (Type UX)

Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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